

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	62mΩ @ V _{GS} = -4.5V	-3.8A
	90mΩ @ V _{GS} = -2.5V	-3.1A

Description and Applications


This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Features and Benefits

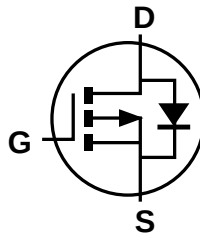
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen- and Antimony-Free. "Green" Device (Note 3)**

Mechanical Data

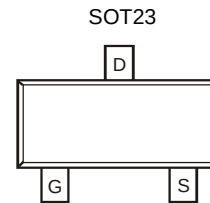
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame.
Solderable per MIL-STD-202, Method 208 
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



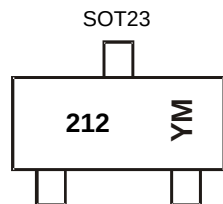
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2120U-7	SOT23	3,000/Tape & Reel
DMP2120U-13	SOT23	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



212 = Product Type Marking Code
 YM = Date Code Marking
 Y or \overline{Y} = Year (ex: H = 2020)
 M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	~	2020	2021	2022	2023	2024	2025
Code	E	~	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current (Note 6) $V_{GS} = -4.5\text{V}$	I_D	-3.8 -3.0	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	-1.3	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	-20	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	163 114	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	94 66	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DS}	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	51 71 116	62 90 150	m Ω	$V_{GS} = -4.5\text{V}, I_D = -4.2\text{A}$ $V_{GS} = -2.5\text{V}, I_D = -3.4\text{A}$ $V_{GS} = -1.8\text{V}, I_D = -2.0\text{A}$
Diode Forward Voltage	V_{SD}	—	-0.7	-1.1	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	487	—	pF	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	60	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	53	—	pF	
Gate Resistance	R_G	—	39	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge	Q_G	—	6.3	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -4\text{V},$ $I_D = -3.5\text{A}$
Gate-Source Charge	Q_{GS}	—	0.7	—	nC	
Gate-Drain Charge	Q_{GD}	—	1.4	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.3	—	ns	$V_{DS} = -4\text{V}, V_{GS} = -4.5\text{V},$ $I_D = -1.0\text{A}, R_G = 6\Omega$
Turn-On Rise Time	t_R	—	15.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	38.5	—	ns	
Turn-Off Fall Time	t_F	—	23.2	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	7.5	—	ns	$I_S = -2.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	1.9	—	nC	$I_S = -2.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

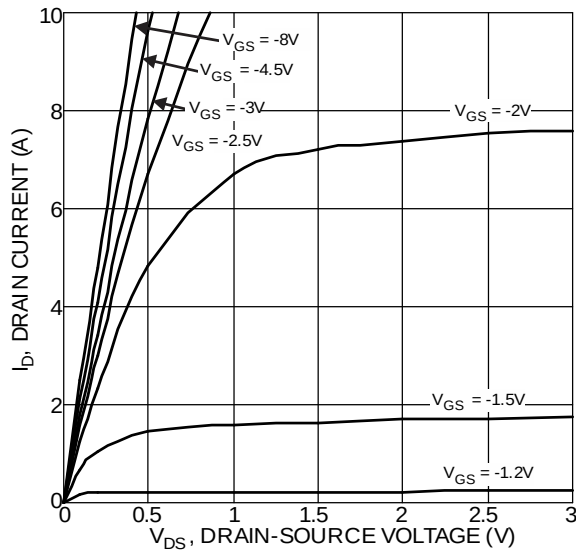


Figure 1 Typical Output Characteristic

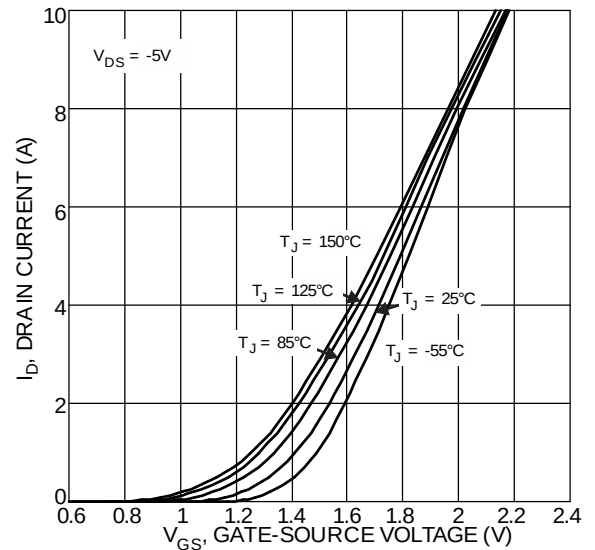


Figure 2 Typical Transfer Characteristics

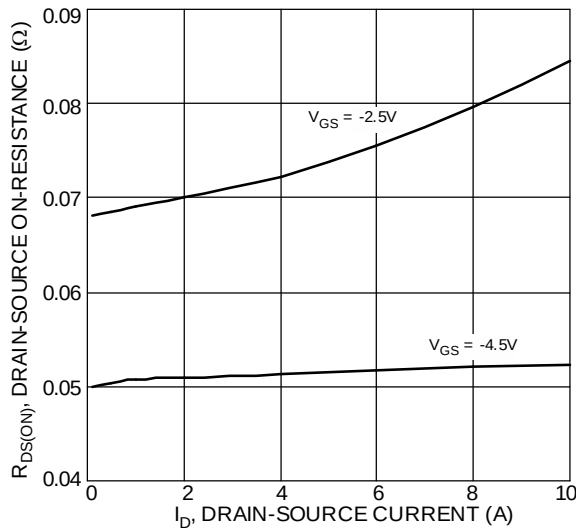


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

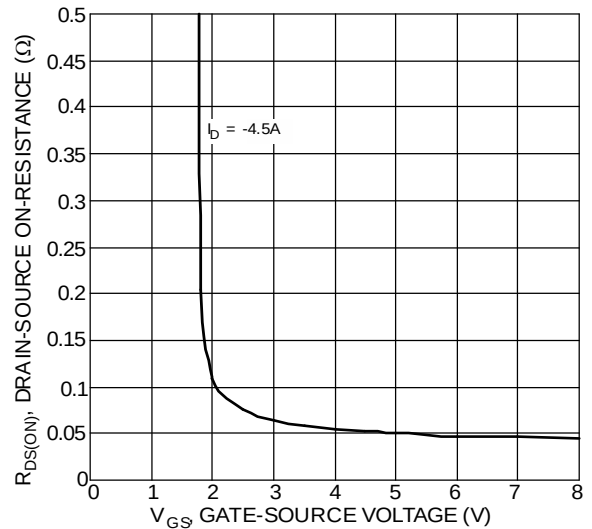


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

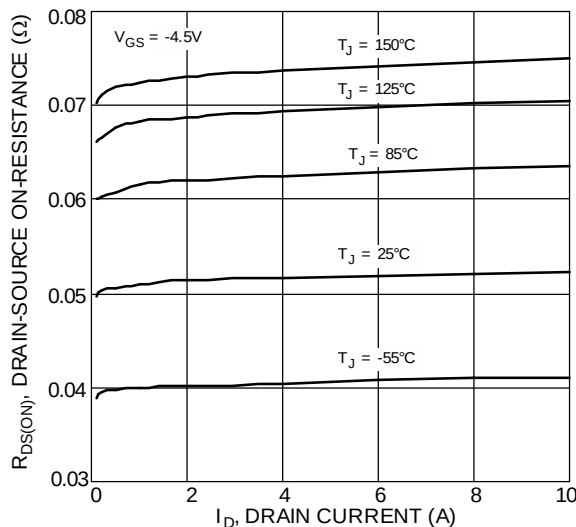


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

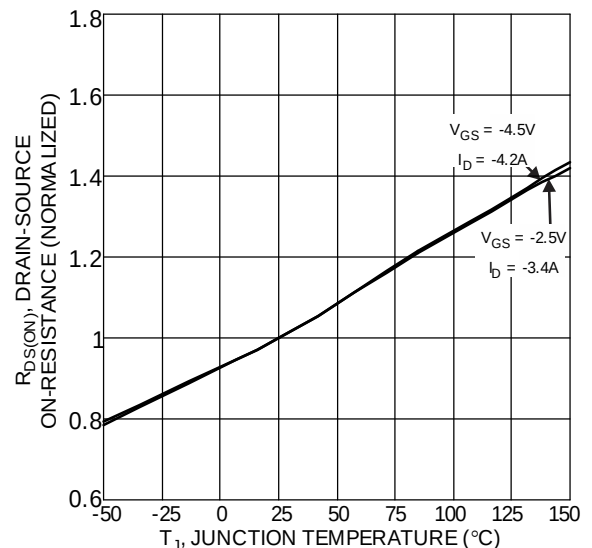
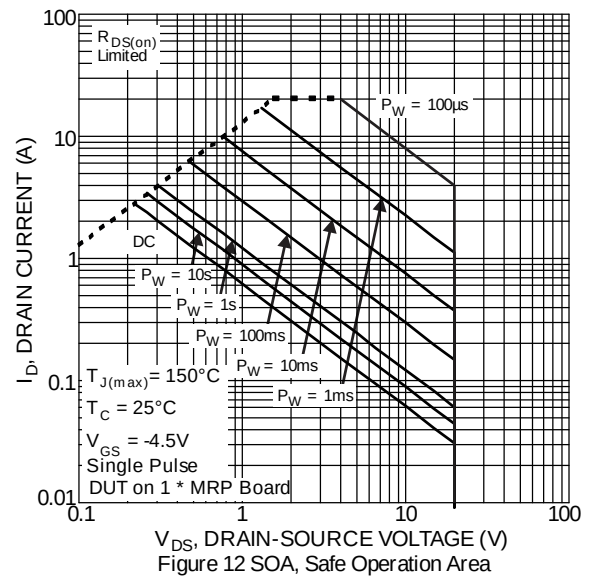
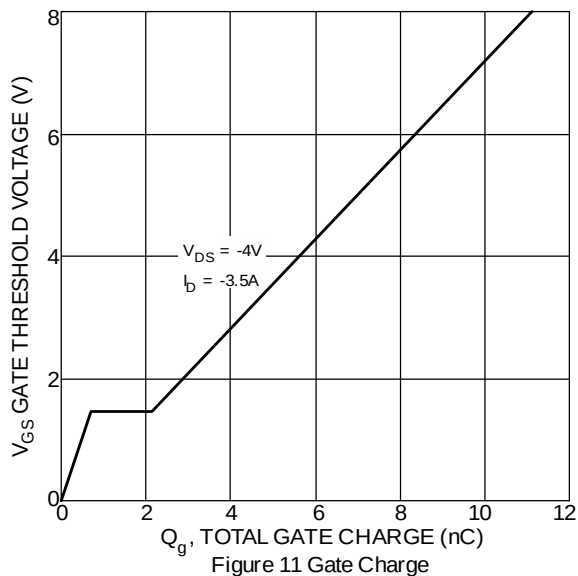
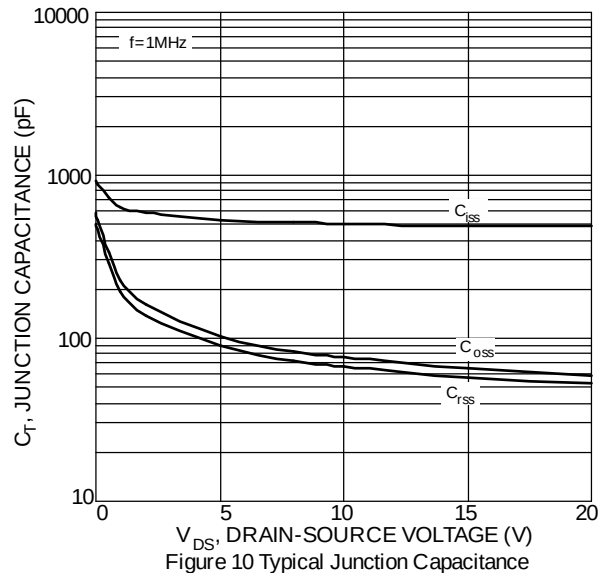
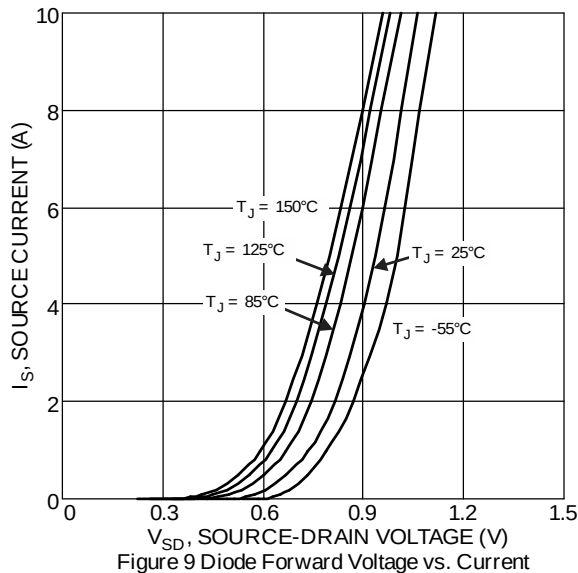
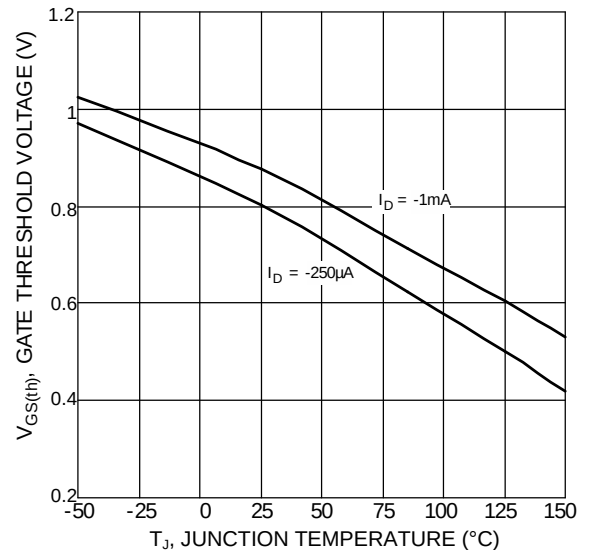
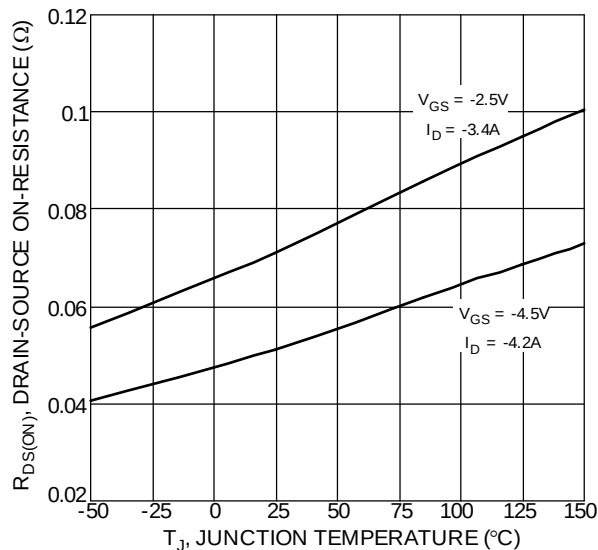
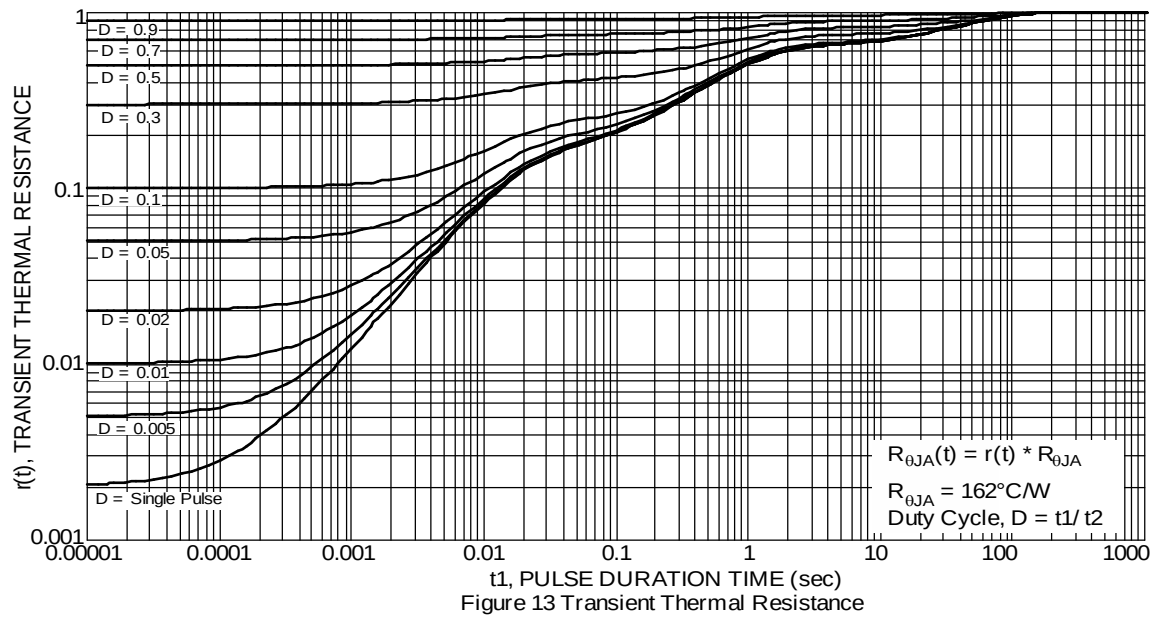


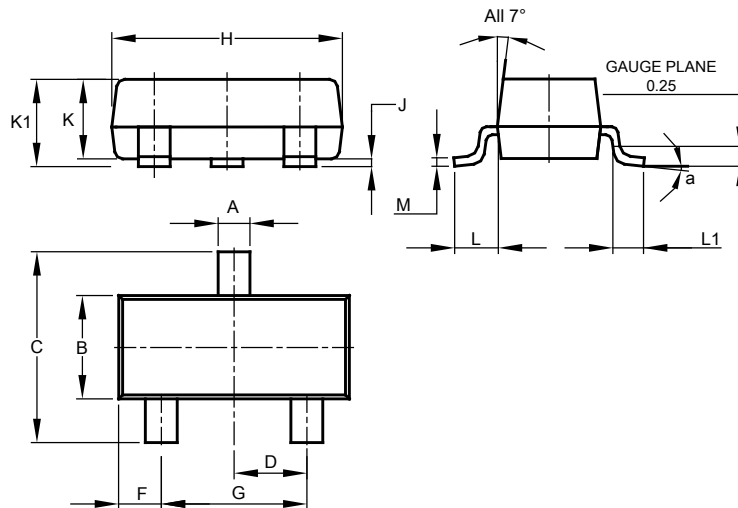
Figure 6 On-Resistance Variation with Temperature





Package Outline Dimensions

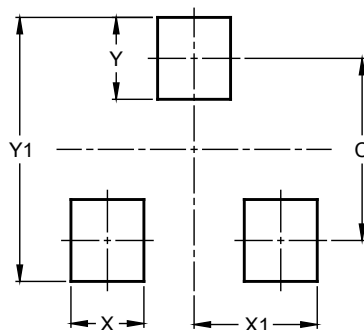
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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